

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)	ATTY DOCKET NO. 3531-0103P	APPLICATION NO. New
APPLICANT Paul R. BERGER et al		FILING DATE August 21, 2001
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<i>dm</i>	Wang YH et al, "RESONANT TUNNELING DIODE IN MBE-GROWN DELTA-DOPED GAAS", Abstract, Electronic Letters, August 29, 1991
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EXAMINER <i>Kang, Donghee</i>	DATE CONSIDERED <i>01-12-05</i>
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<i>DNL</i>	K. ISMAIL et al, "ELECTRON RESONANT TUNNELING IN Si/SiGe DOUBLE BARRIER DIODES", Applied Physics Letters, 59, (8), August 19, 1991
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